

BIPOLAR ANALOG INTEGRATED CIRCUIT $\mu PC4082$

J-FET INPUT DUAL OPERATIONAL AMPLIFIER

DESCRIPTION

The μ PC4082 is a dual operational amplifier incorporating well matched ion implant P-channel J-FET on the same chip with standard bipolar transistors. The key features of this op amp is very low input bias current and high slew rate for ten times faster than conventional general purpose op amps. By these features the μ PC4082 is excellent choice for wide variety of applications including integrator, active filter, pulse amp etc.

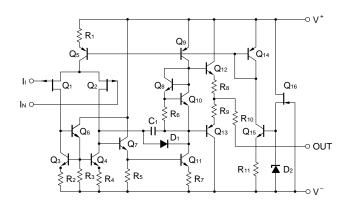
FEATURES

- Low noise: $e_n = 25 \text{ nV}/\sqrt{\text{Hz}}$ (TYP.)
- · Very low input bias and offset currents
- · Output short circuit protection
- High input impedance...J-FET Input stage
- · Internal frequency compensation
- High slew rate...13 V/μs (TYP.)

ORDERING INFORMATION

| Part Number | Package |
|-------------|-----------------------------------|
| μPC4082C | 8-pin plastic DIP (7.62 mm (300)) |
| μPC4082G2 | 8-pin plastic SOP (5.72 mm (225)) |

EQUIVALENT CIRCUIT



PIN CONFIGURATION (Top View)

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

| Par | ameter | Symbol | Ratings | Unit |
|----------------------------------|---------------------------|---------|--------------------------------------------|------|
| Voltage between V ⁺ a | and V ^{- Note 1} | V* - V_ | -0.3 to +36 | V |
| Differential Input Volta | age | VID | ±30 | ٧ |
| Input Voltage Note 2 | | Vı | V ⁻ -0.3 to V ⁺ +0.3 | V |
| Output Voltage Note 3 | | Vo | V ⁻ -0.3 to V ⁺ +0.3 | V |
| Power Dissipation | C Package Note 4 | PT | 350 | mW |
| | G2 Package Note 5 | | 440 | mW |
| Output Short Circuit D | Ouration Note 6 | | Indefinite | sec |
| Operating Ambient Temperature | | TA | -20 to +80 | °C |
| Storage Temperature | | Tstg | -55 to +125 | °C |

- Notes 1. Reverse connection of supply voltage can cause destruction.
 - 2. The input voltage should be allowed to input without damage or destruction. Even during the transition period of supply voltage, power on/off etc., this specification should be kept. The normal operation will establish when the both inputs are within the Common Mode Input Voltage Range of electrical characteristics.
 - 3. This specification is the voltage which should be allowed to supply to the output terminal from external without damage or destructive. Even during the transition period of supply voltage, power on/off etc., this specification should be kept. The output voltage of normal operation will be the Output Voltage Swing of electrical characteristics.
 - 4. Thermal derating factor is -5.0 mV/°C when operating ambient temperature is higher than 55°C.
 - 5. Thermal derating factor is -4.4 mV/°C when operating ambient temperature is higher than 25°C.
 - **6.** Pay careful attention to the total power dissipation not to exceed the absolute maximum ratings, Note 4 and Note 5.

RECOMMENDED OPERATING CONDITIONS

| Parameter | Symbol | MIN. | TYP. | MAX. | Unit |
|---------------------------------------------------------|----------------|------|------|------|------|
| Supply Voltage | V [±] | ±5 | | ±16 | V |
| Output Current | lo | | | ±10 | mA |
| Capacitive Load (Av = +1, R _f = 0 Ω) | CL | | | 100 | pF |

*



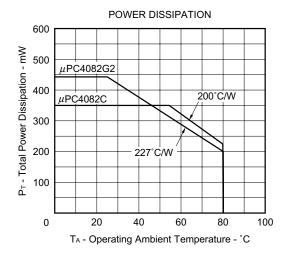
ELECTRICAL CHARACTERISTICS (TA = 25°C, V^{\pm} = ± 15 V)

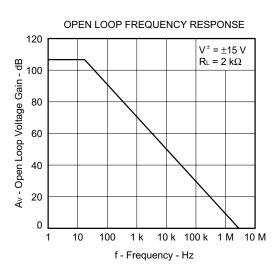
| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|-------------------------------------------|------------|---------------------------------------------|-------|--------|------|--------------------|
| Input Offset Voltage | Vio | Rs ≤ 50 Ω | | ±5 | ±15 | mV |
| Input Offset Current Note 7 | lio | | | ±5 | ±200 | рА |
| Input Bias Current Note 7 | Ів | | | 30 | 400 | рА |
| Large Signal Voltage Gain | Av | $R_L \geq 2~k\Omega$, $V_0 = \pm 10~V$ | 25000 | 200000 | | |
| Supply Current | Icc | Io = 0 A, Both Amplifiers | | 4.0 | 5.6 | mA |
| Common Mode Rejection Ratio | CMR | | 70 | 76 | | dB |
| Supply Voltage Rejection Ratio | SVR | | 70 | 76 | | dB |
| Output Voltage Swing | Vom | R _L ≥ 10 kΩ | ±12 | ±13.5 | | V |
| | | $R_L \ge 2 \ k\Omega$ | ±10 | ±12 | | V |
| Common Model Input Voltage Range | Vісм | | ±10 | +15 | | V |
| | | | | -12.7 | | |
| Slew Rate | SR | Av = 1 | | 13 | | V/μs |
| Unity Gain Frequency | funity | | | 3 | | MHz |
| Input Equivalent Noise Voltage Density | e n | Rs = 100 Ω , f = 1 kHz | | 25 | | nV/√ Hz |
| Channel Separation | | | | 120 | | dB |
| Input Offset Voltage | Vio | Rs \leq 50 Ω , TA = -20 to +70°C | | | ±20 | mV |
| Average V ₁₀ Temperature Drift | ΔV10/ΔΤ | $T_A = -20 \text{ to } +70^{\circ}\text{C}$ | | ±10 | | μV/°C |
| Input Offset Current Note 7 | lio | T _A = -20 to +70°C | | | ±5 | nA |
| Input Bias Current Note 7 | Ів | $T_A = -20 \text{ to } +70^{\circ}\text{C}$ | | | 10 | nA |

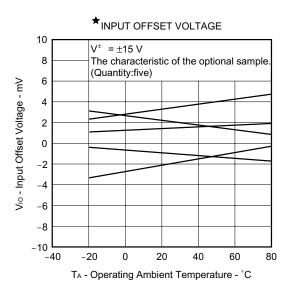
Notes 7. Input bias currents flow into IC. Because each currents are gate leak current of P-channel J-FET on input stage. And that are temperature sensitive. Short time measuring method is recommendable to maintain the junction temperature close to the operating ambient temperature.

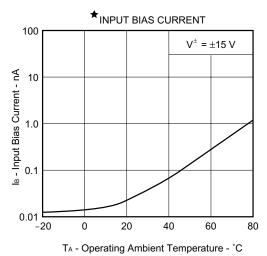
Data Sheet G15378EJ3V0DS 3

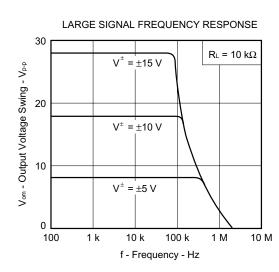
TYPICAL PERFORMANCE CHARACTERISTICS (TA = 25°C, TYP.)

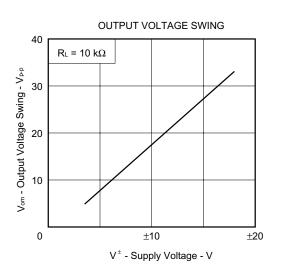


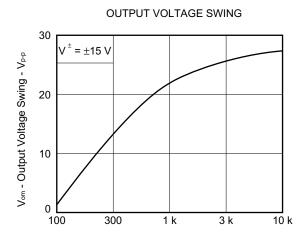




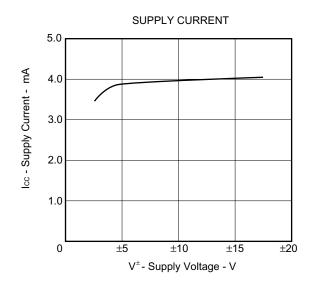




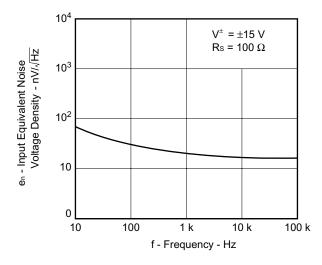




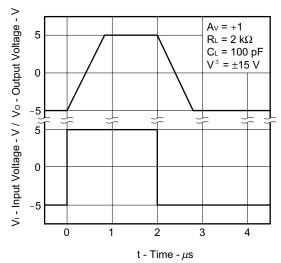




INPUT EQUIVALENT NOISE VOLTAGE DENSITY

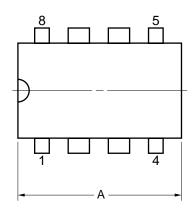


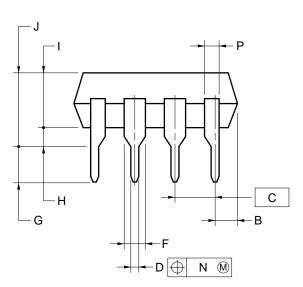
VOLTAGE FOLLOWER PULSE RESPONSE

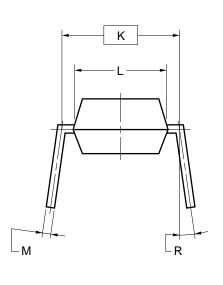


★ PACKAGE DRAWINGS (Unit:mm)

8-PIN PLASTIC DIP (7.62mm(300))







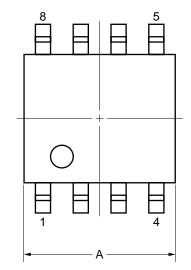
NOTES

- 1. Each lead centerline is located within 0.25 mm of its true position (T.P.) at maximum material condition.
- 2. Item "K" to center of leads when formed parallel.

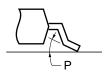
| ITEM | MILLIMETERS |
|------|------------------------|
| Α | 10.16 MAX. |
| В | 1.27 MAX. |
| С | 2.54 (T.P.) |
| D | 0.50±0.10 |
| F | 1.4 MIN. |
| G | 3.2±0.3 |
| Н | 0.51 MIN. |
| I | 4.31 MAX. |
| J | 5.08 MAX. |
| K | 7.62 (T.P.) |
| L | 6.4 |
| М | $0.25^{+0.10}_{-0.05}$ |
| N | 0.25 |
| Р | 0.9 MIN. |
| R | 0~15° |
| | |

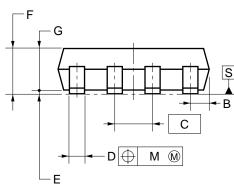
P8C-100-300B,C-2

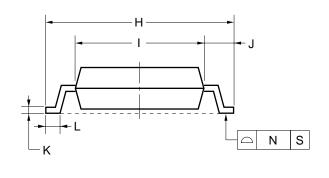
8-PIN PLASTIC SOP (5.72 mm (225))



detail of lead end







NOTE

Each lead centerline is located within 0.12 mm of its true position (T.P.) at maximum material condition.

| MILLIMETERS |
|------------------------|
| $5.2_{-0.20}^{+0.17}$ |
| 0.78 MAX. |
| 1.27 (T.P.) |
| $0.42^{+0.08}_{-0.07}$ |
| 0.1±0.1 |
| 1.59±0.21 |
| 1.49 |
| 6.5±0.3 |
| 4.4±0.15 |
| 1.1±0.2 |
| $0.17^{+0.08}_{-0.07}$ |
| 0.6±0.2 |
| 0.12 |
| 0.10 |
| 3°+7° |
| |

S8GM-50-225B-6

★ RECOMMENDED SOLDERING CONDITIONS

When soldering this product, it is highly recommended to observe the conditions as shown below. If other soldering processes are used, or if the soldering is performed under different conditions, please make sure to consult with our sales offices.

For more details, refer to our document "SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL" (C10535E).

Type of Surface Mount Device

μPC4082G2: 8-pin plastic SOP (5.72 mm (225))

| Process | Conditions | Symbol |
|------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------|
| Infrared Ray Reflow | Peak temperature: 230°C or below (Package surface temperature), Reflow time: 30 seconds or less (at 210°C or higher), Maximum number of reflow processes: 1 time. | IR30-00-1 |
| Vapor Phase Soldering | Peak temperature: 215°C or below (Package surface temperature), Reflow time: 40 seconds or less (at 200°C or higher), Maximum number of reflow processes: 1 time. | VP15-00-1 |
| Wave Soldering | Solder temperature: 260°C or below, Flow time: 10 seconds or less, Maximum number of flow processes: 1 time, Pre-heating temperature: 120°C or below (Package surface temperature). | WS60-00-1 |
| Partial Heating Method | Pin temperature: 300°C or below, Heat time: 3 seconds or less (Per each side of the device). | - |

Caution Apply only one kind of soldering condition to a device, except for "partial heating method", or the device will be damaged by heat stress.

Type of Through-hole Device

 μ PC4082C: 8-pin plastic DIP (7.62 mm (300))

| Process | Conditions |
|------------------------|--------------------------------------------------------------------------------|
| Wave Soldering | Solder temperature: 260°C or below, |
| (only to leads) | Flow time: 10 seconds or less. |
| Partial Heating Method | Pin temperature: 300°C or below, Heat time: 3 seconds or less (per each lead). |

Caution For through-hole device, the wave soldering process must be applied only to leads, and make sure that the package body does not get jet soldered.

NEC μ PC4082

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NEC μ PC4082

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M8E 00.4